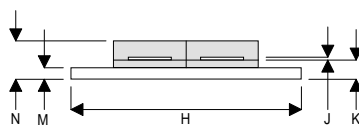
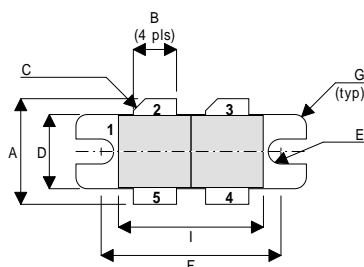


MECHANICAL DATA

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
100W – 28V – 500MHz  
PUSH-PULL**



DH

PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2
PIN 5	GATE 1		

DIM	mm	Tol.	Inches	Tol.
A	13.97	0.26	0.550	0.010
B	5.72	0.13	0.225	0.005
C	45°	5°	45°	5°
D	9.78	0.13	0.385	0.005
E	1.65R	0.13	0.065R	0.005
F	23.75	0.13	0.935	0.005
G	1.52R	0.13	0.060R	0.005
H	30.48	0.13	1.200	0.005
I	19.17	0.26	0.755	0.010
J	0.13	0.02	0.005	0.001
K	2.54	0.13	0.100	0.005
M	1.52	0.13	0.060	0.005
N	5.08	0.50	0.200	0.020

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS  
from 1 MHz to 500 MHz

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	290W
$BV_{DSS}$	Drain – Source Breakdown Voltage *	70V
$BV_{GSS}$	Gate – Source Breakdown Voltage *	$\pm 20V$
$I_{D(sat)}$	Drain Current *	15A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

\* Per Side

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>PER SIDE</b>					
B <sub>V</sub> DSS	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0	I <sub>D</sub> = 100mA	70	V
I <sub>D</sub> DSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0	3	mA
I <sub>G</sub> DSS	Gate Leakage Current	V <sub>GS</sub> = 20V	V <sub>DS</sub> = 0	1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage*	I <sub>D</sub> = 10mA	V <sub>DS</sub> = V <sub>GS</sub>	1	V
g <sub>fs</sub>	Forward Transconductance*	V <sub>DS</sub> = 10V	I <sub>D</sub> = 3A	2.4	S
<b>TOTAL DEVICE</b>					
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 100W		10	dB
η	Drain Efficiency	V <sub>DS</sub> = 28V	I <sub>DQ</sub> = 1.2A	50	%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1	—
<b>PER SIDE</b>					
C <sub>i</sub> SS	Input Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = -5V f = 1MHz		180 pF
C <sub>o</sub> SS	Output Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0 f = 1MHz		90 pF
C <sub>r</sub> SS	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0 f = 1MHz		7.5 pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 0.6°C / W
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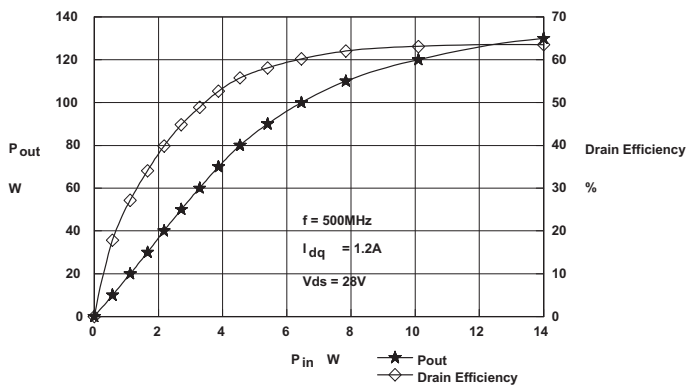


Figure 1 - Power Output and Efficiency vs. Power Input.

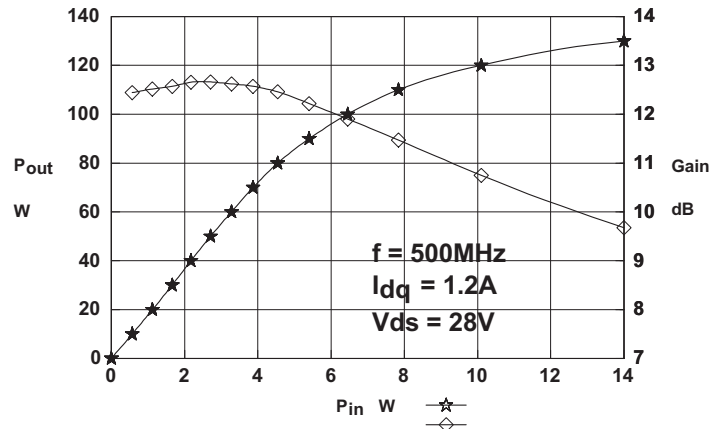


Figure 2 - Power Output & Gain vs. Power Input.

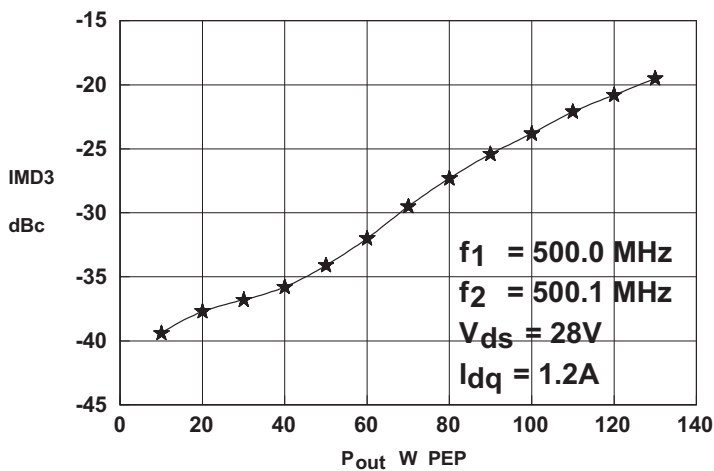
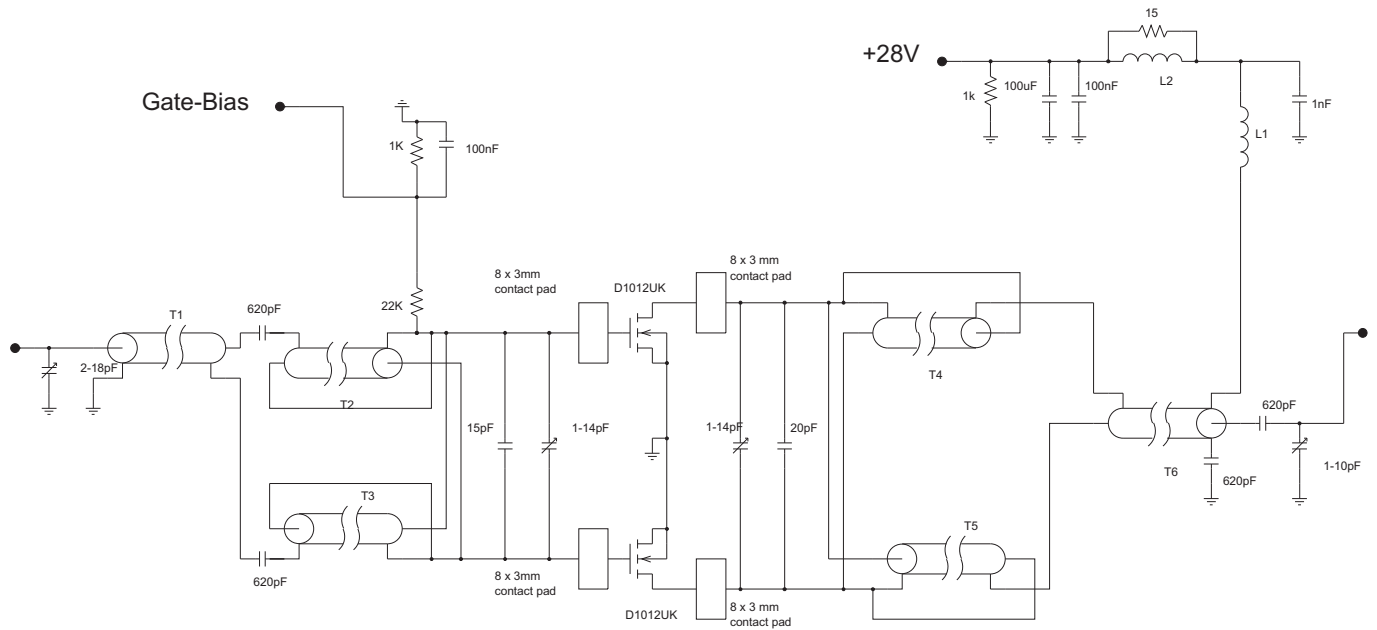


Figure 3 - IMD vs. Output Power.

### D1012UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
500	2.0 - j2.2	2.6 - j0.6

N.B. Impedances measured terminal to terminal



## D1012UK 500MHz TEST FIXTURE

T1,6	65mm	50 Ohm UT85 semi-rigid coax
T2,3,4,5	75mm	15 Ohm UT85-15 semi-rigid coax
L1	6 turns	21 swg enamelled copper wire, 3mm i.d.
L2	8.5 turns	19 swg enamelled copper wire on Fair-Rite FT82-43 core